

Features

- Designed for soft commutation only
- Maximum junction temperature: $T_J = 175\text{ }^\circ\text{C}$
- Minimized tail current
- $V_{CE(sat)} = 2.0\text{ V (typ.) @ } I_C = 15\text{ A}$
- Tight parameters distribution
- Safe paralleling
- Very low V_F soft recovery co-packaged diode
- Low thermal resistance
- Lead free package

Applications

- Induction heating
- Microwave oven
- Resonant converters

Description

These IGBTs are developed using an advanced proprietary trench gate field-stop structure and performance is optimized in both conduction and switching losses. A freewheeling diode with a low drop forward voltage is co-packaged. The result is a product specifically designed to maximize efficiency for any resonant and soft-switching application.

Figure 1. Internal schematic diagram

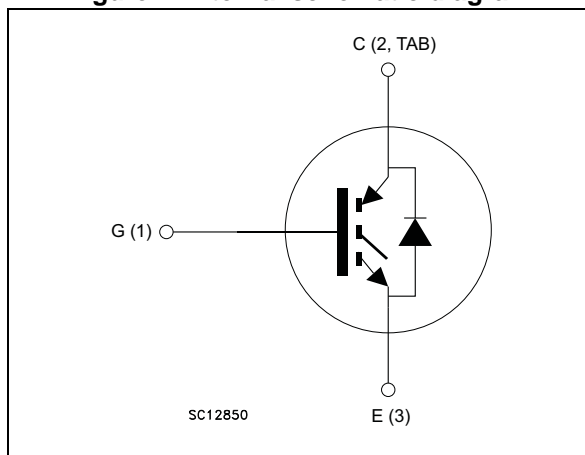


Table 1. Device summary

| Order code | Marking | Package | Packaging |
|----------------|------------|---------|-----------|
| STGW20IH125DF | G20IH125DF | TO-247 | Tube |
| STGWT20IH125DF | G20IH125DF | TO-3P | Tube |

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1 Electrical ratings

Table 2. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|---|-------------|------|
| V_{CES} | Collector-emitter voltage ($V_{GE} = 0$) | 1250 | V |
| I_C | Continuous collector current at $T_C = 25\text{ °C}$ | 40 | A |
| I_C | Continuous collector current at $T_C = 100\text{ °C}$ | 20 | A |
| $I_{CP}^{(1)}$ | Pulsed collector current | 80 | A |
| V_{GE} | Gate-emitter voltage | ± 20 | V |
| I_F | Continuous forward current at $T_C = 25\text{ °C}$ | 40 | A |
| I_F | Continuous forward current at $T_C = 100\text{ °C}$ | 20 | A |
| $I_{FP}^{(1)}$ | Pulsed forward current | 80 | A |
| P_{TOT} | Total dissipation at $T_C = 25\text{ °C}$ | 259 | W |
| T_{STG} | Storage temperature range | - 55 to 150 | °C |
| T_J | Operating junction temperature | - 55 to 175 | °C |

1. Pulse width limited by maximum junction temperature

Table 3. Thermal data

| Symbol | Parameter | Value | Unit |
|------------|--|-------|------|
| R_{thJC} | Thermal resistance junction-case IGBT | 0.58 | °C/W |
| R_{thJC} | Thermal resistance junction-case diode | 1.47 | °C/W |
| R_{thJA} | Thermal resistance junction-ambient | 50 | °C/W |

2 Electrical characteristics

$T_J = 25\text{ °C}$ unless otherwise specified.

Table 4. Static characteristics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--|--|------|------|------|---------------|
| $V_{(BR)CES}$ | Collector-emitter breakdown voltage ($V_{GE} = 0$) | $I_C = 2\text{ mA}$ | 1250 | | | V |
| $V_{CE(sat)}$ | Collector-emitter saturation voltage | $V_{GE} = 15\text{ V}, I_C = 15\text{ A}$ | | 2 | 2.5 | V |
| | | $V_{GE} = 15\text{ V}, I_C = 15\text{ A}$ $T_J = 125\text{ °C}$ | | 2.2 | | |
| | | $V_{GE} = 15\text{ V}, I_C = 15\text{ A}$ $T_J = 175\text{ °C}$ | | 2.3 | | |
| | | $V_{GE} = 15\text{ V}, I_C = 30\text{ A}$ | | 2.55 | | |
| V_F | Forward on-voltage | $I_F = 15\text{ A}$ | | 1.1 | 1.5 | V |
| | | $I_F = 15\text{ A } T_J = 125\text{ °C}$ | | 1.05 | | |
| | | $I_F = 15\text{ A } T_J = 175\text{ °C}$ | | 1 | | |
| | | $I_F = 30\text{ A}$ | | 1.25 | | |
| $V_{GE(th)}$ | Gate threshold voltage | $V_{CE} = V_{GE}, I_C = 500\text{ }\mu\text{A}$ | 5 | 6 | 7 | V |
| I_{CES} | Collector cut-off current ($V_{GE} = 0$) | $V_{CE} = 1250\text{ V}$ | | | 25 | μA |
| I_{GES} | Gate-emitter leakage current ($V_{CE} = 0$) | $V_{GE} = \pm 20\text{ V}$ | | | 250 | nA |

Table 5. Dynamic characteristics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------|------------------------------|--|------|------|------|------|
| C_{ies} | Input capacitance | $V_{CE} = 25\text{ V}, f = 1\text{ MHz},$ $V_{GE} = 0$ | - | 1290 | - | pF |
| C_{oes} | Output capacitance | | - | 96 | - | pF |
| C_{res} | Reverse transfer capacitance | | - | 30.6 | - | pF |
| Q_g | Total gate charge | $V_{CC} = 600\text{ V}, I_C = 15\text{ A},$ $V_{GE} = 15\text{ V},$ see Figure 25 | - | 69 | - | nC |
| Q_{ge} | Gate-emitter charge | | - | 7.2 | - | nC |
| Q_{gc} | Gate-collector charge | | - | 40.8 | - | nC |

Table 6. IGBT switching characteristics (inductive load)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|---------------------------|---|------|------|------|---------------|
| $t_{d(off)}$ | Turn-off delay time | $V_{CE} = 600\text{ V}$, $I_C = 15\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, see Figure 23 | | 106 | | ns |
| t_f | Current fall time | | - | 79 | - | ns |
| $E_{off}^{(1)}$ | Turn-off switching losses | | - | 410 | - | μJ |
| $t_{d(off)}$ | Turn-off delay time | $V_{CE} = 600\text{ V}$, $I_C = 15\text{ A}$, $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 175\text{ }^\circ\text{C}$, see Figure 23 | | 109 | | ns |
| t_f | Current fall time | | - | 176 | - | ns |
| $E_{off}^{(1)}$ | Turn-off switching losses | | - | 820 | - | μJ |

1. Turn-off losses include also the tail of the collector current.

Table 7. IGBT switching characteristics (capacitive load)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|---------------------------|---|------|------|------|---------------|
| $E_{off}^{(1)}$ | Turn-off switching losses | $V_{CC} = 900\text{ V}$, $R_G = 10\ \Omega$, $I_C = 30\text{ A}$, $L = 500\ \mu\text{H}$, $C_{snub} = 330\text{ nF}$, see Figure 24 | - | 163 | - | μJ |
| | | $V_{CC} = 900\text{ V}$, $R_G = 10\ \Omega$, $I_C = 30\text{ A}$, $L = 500\ \mu\text{H}$, $C_{snub} = 330\text{ nF}$, $T_J = 175\text{ }^\circ\text{C}$, see Figure 24 | - | 366 | - | |

1. Turn-off losses include also the tail of the collector current.

2.1 Electrical characteristics (curves)

Figure 2. Power dissipation vs. case temperature

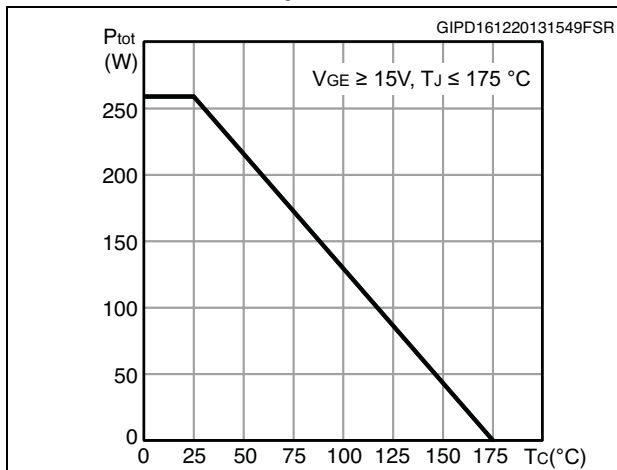


Figure 3. Collector current vs. case temperature

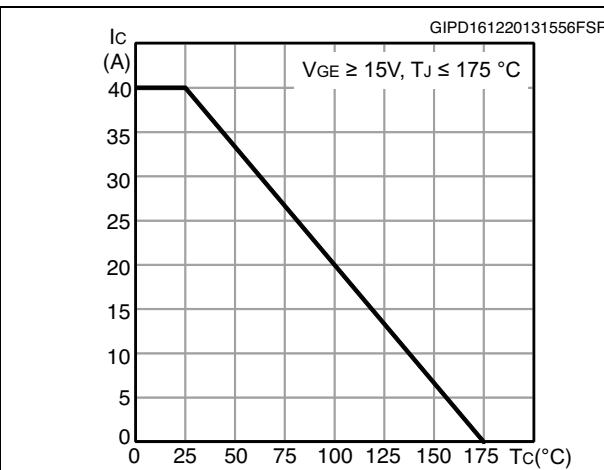


Figure 4. Output characteristics (T_J = 25°C)

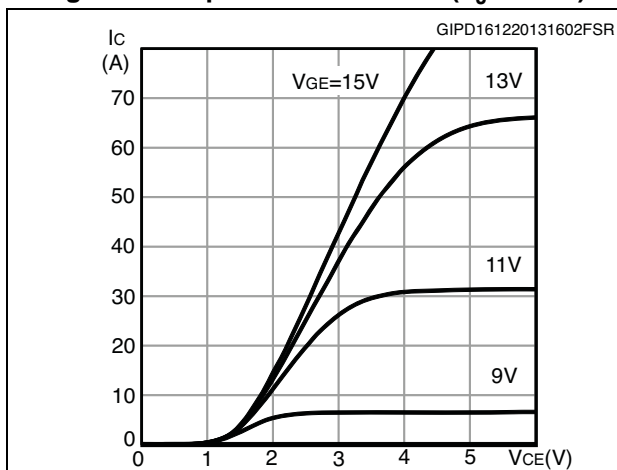


Figure 5. Output characteristics (T_J = 175°C)

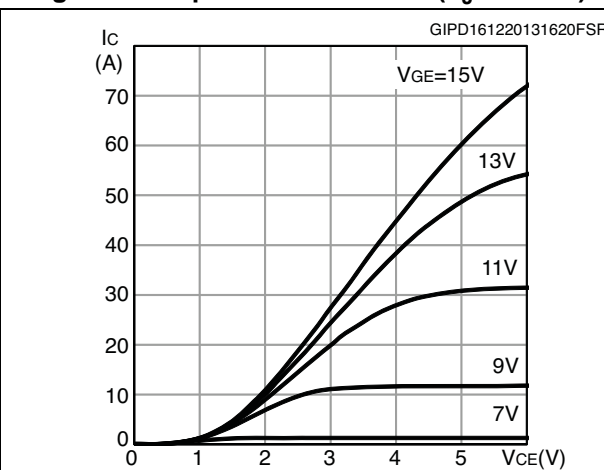


Figure 6. V_{CE(sat)} vs. junction temperature

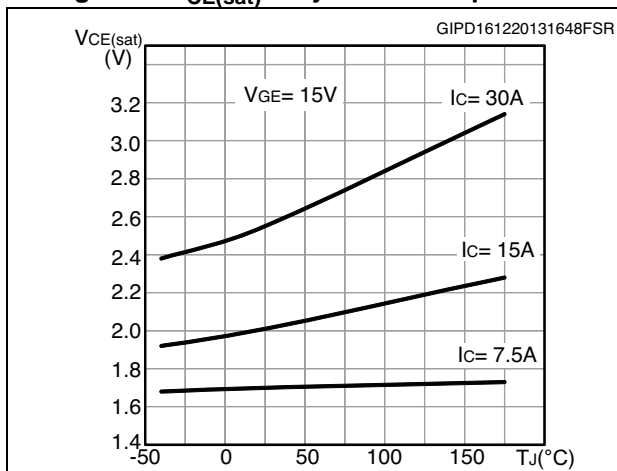


Figure 7. V_{CE(sat)} vs. collector current

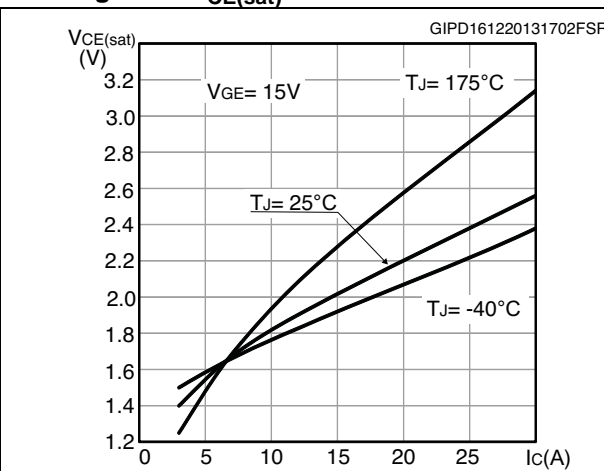


Figure 8. Forward bias safe operating area

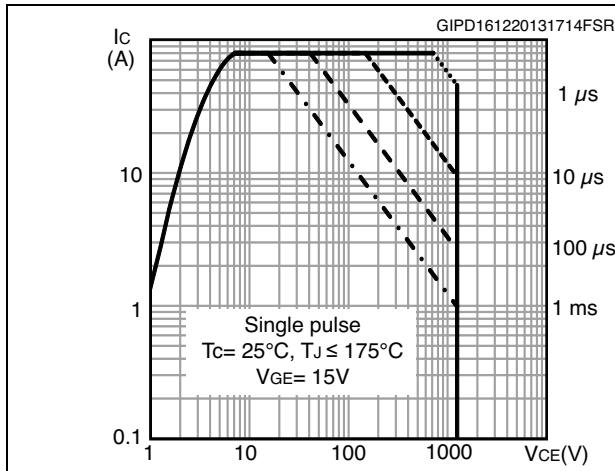


Figure 9. Transfer characteristics

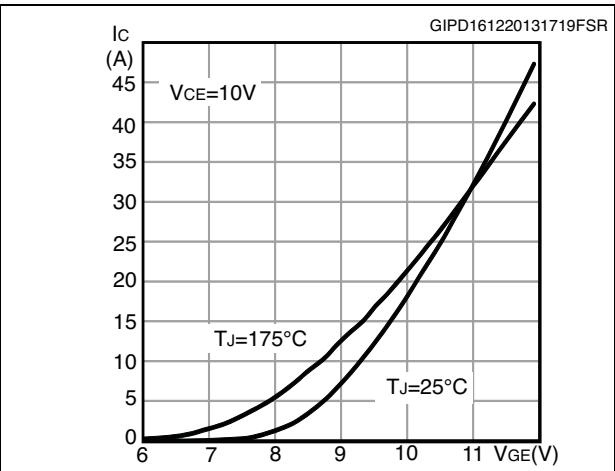


Figure 10. Diode V_F vs. forward current

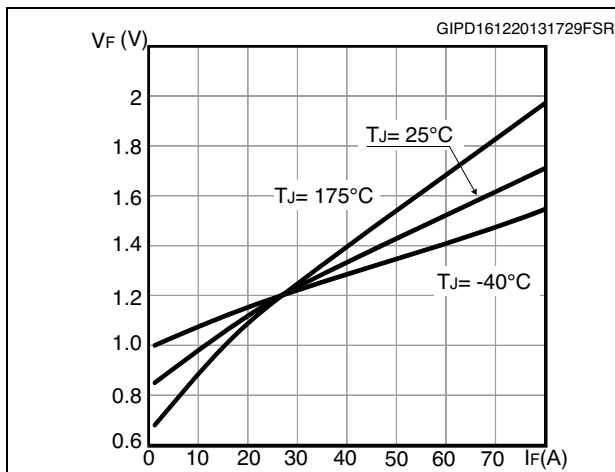


Figure 11. Normalized V_{GE(th)} vs junction temperature



Figure 12. Normalized V_{(BR)CES} vs. junction temperature

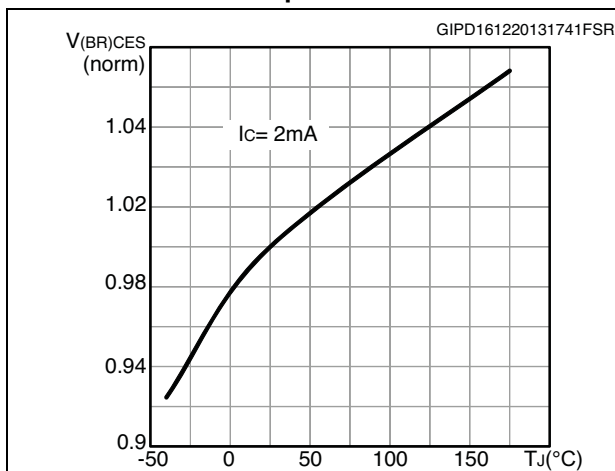


Figure 13. Capacitance variation

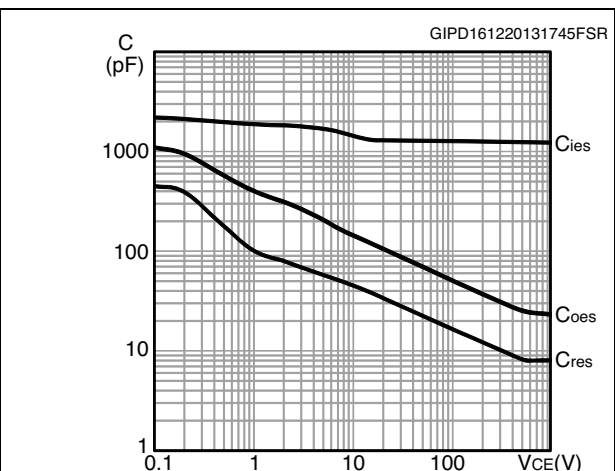


Figure 14. Gate charge vs. gate-emitter voltage

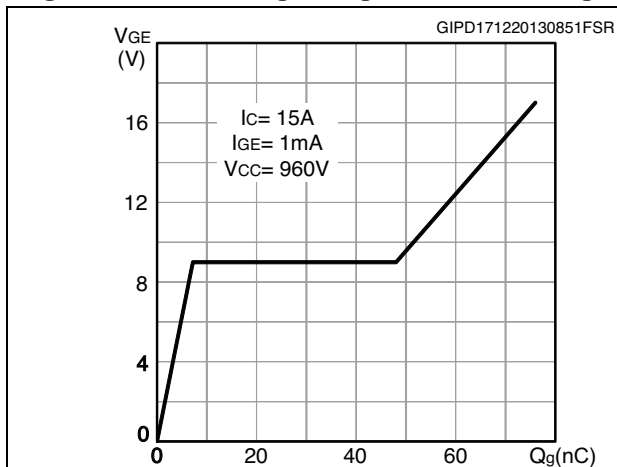


Figure 15. Switching loss vs collector current

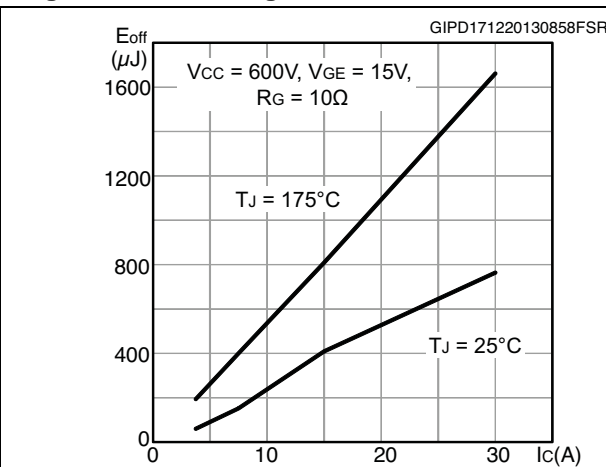


Figure 16. Switching-off loss vs gate resistance

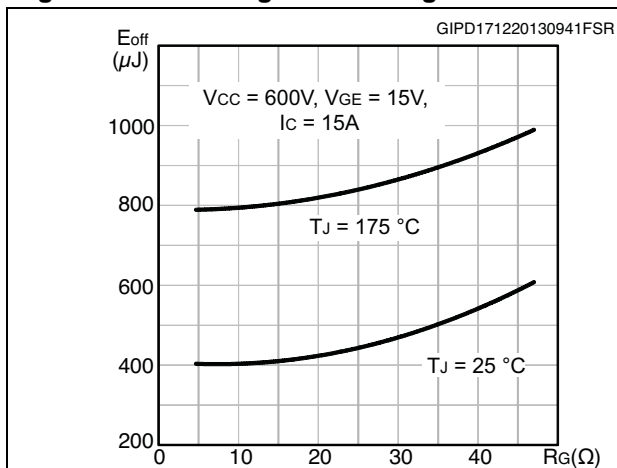


Figure 17. Switching-off loss vs temperature

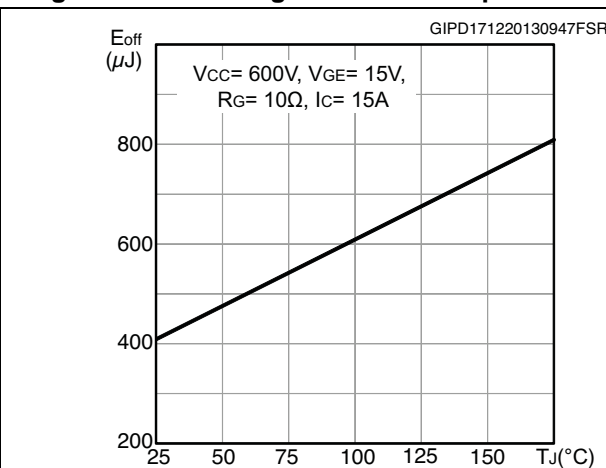


Figure 18. Switching-off loss vs collector-emitter voltage

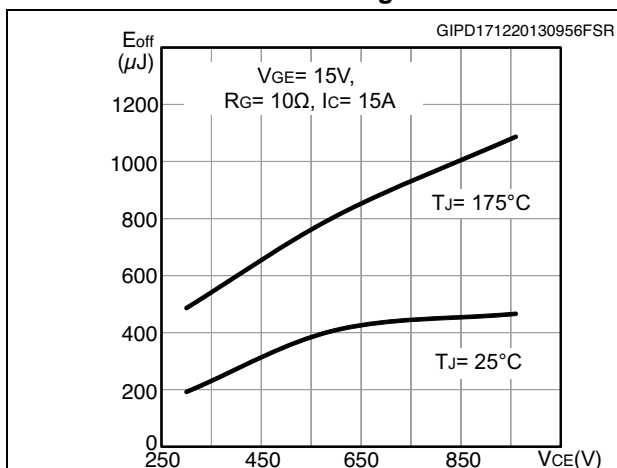


Figure 19. Switching times vs. collector current

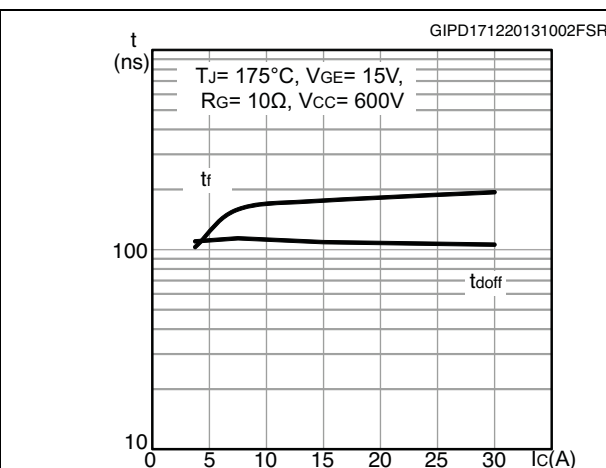


Figure 20. Switching times vs. gate resistance

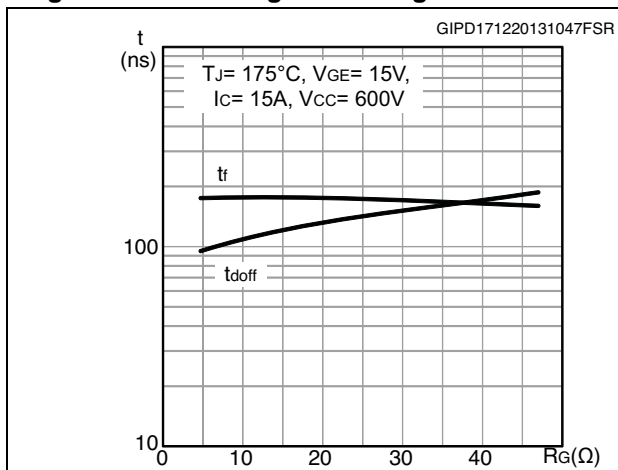


Figure 21. Thermal impedance for IGBT

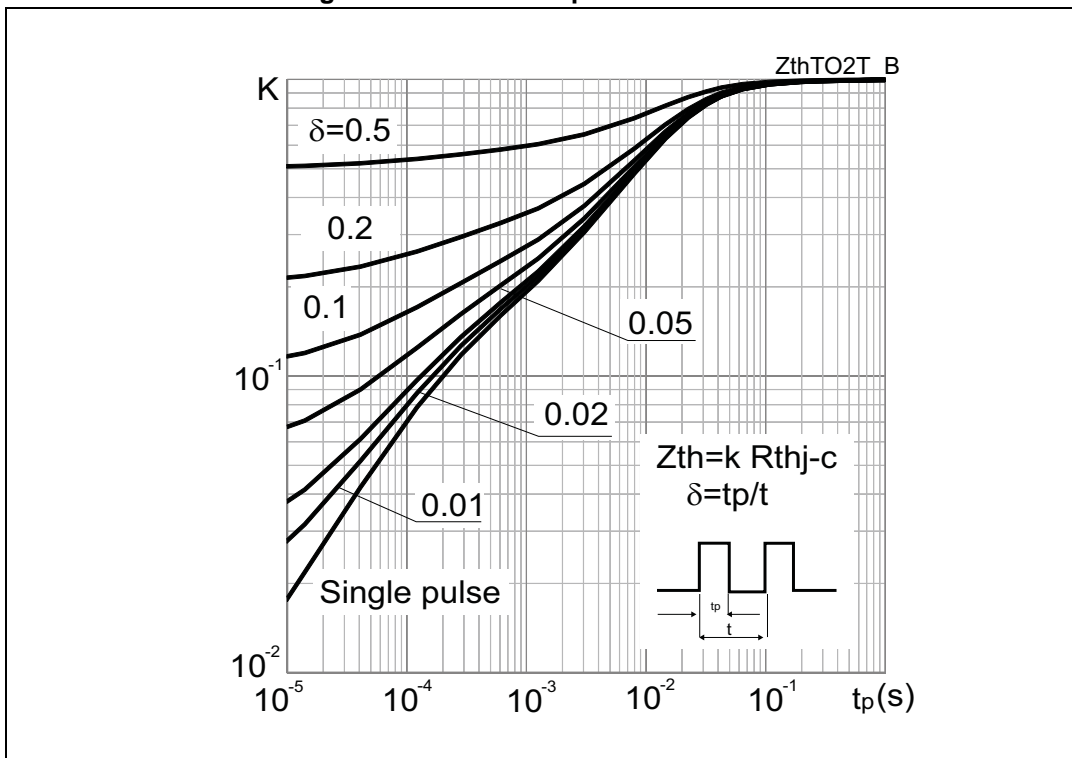
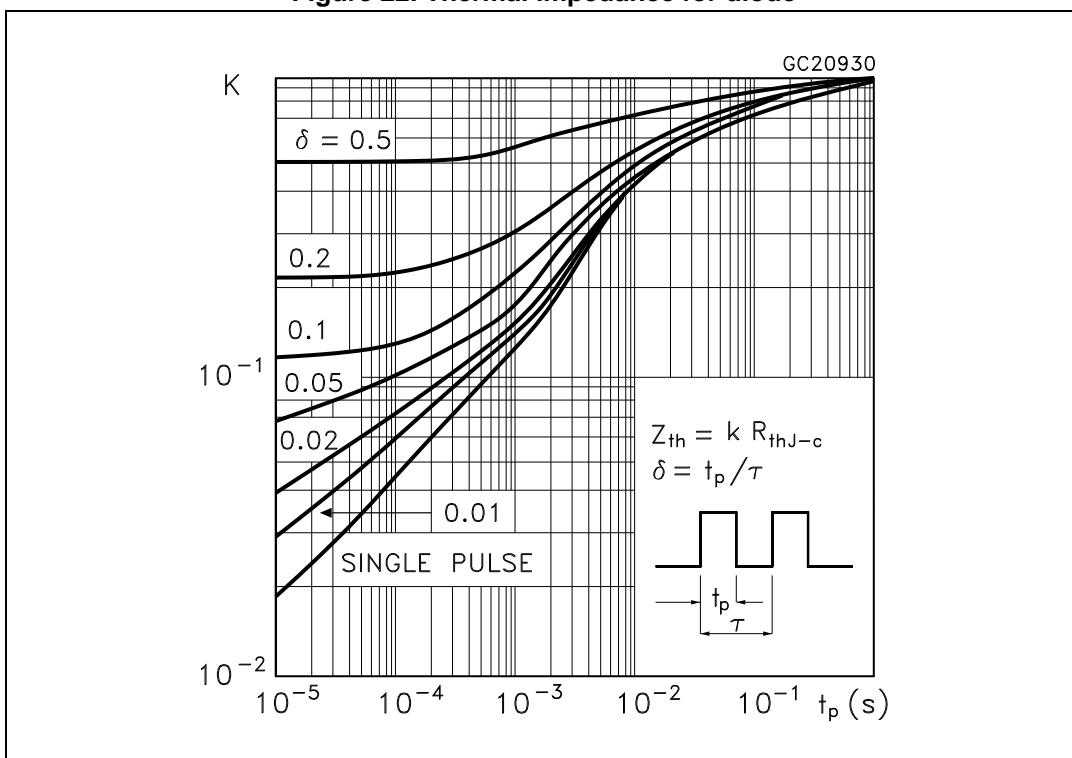


Figure 22. Thermal impedance for diode



3 Test circuits

Figure 23. Test circuit for inductive load switching

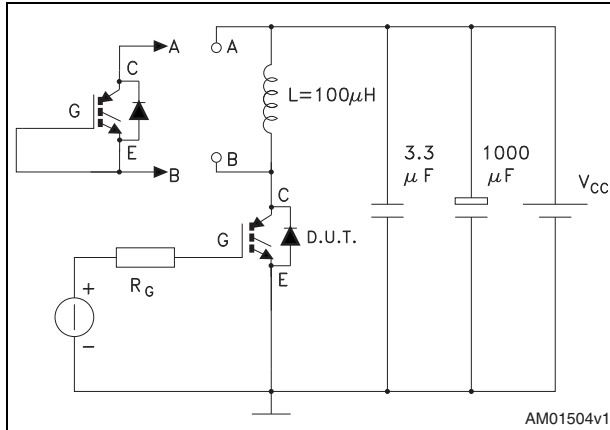


Figure 24. Test circuit for capacitive load switching

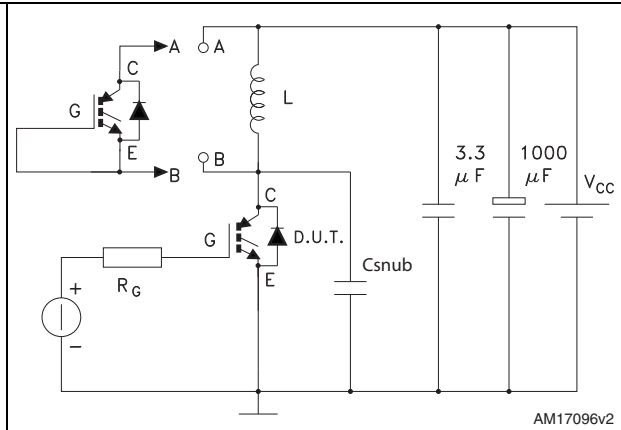


Figure 25. Gate charge test circuit

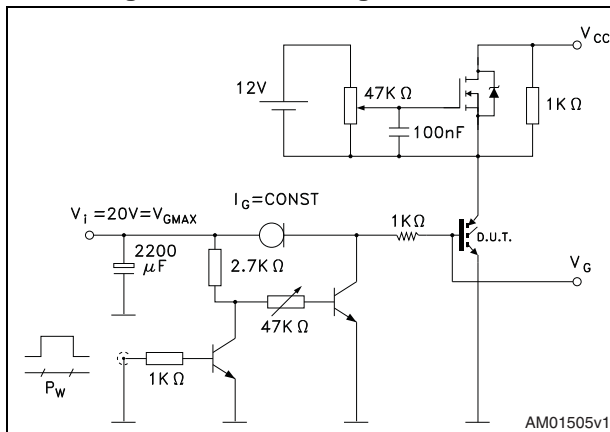
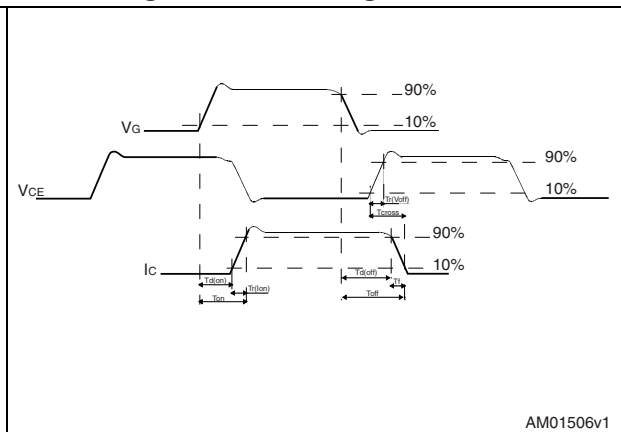


Figure 26. Switching waveform



4 Package mechanical data

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Figure 27. TO-247 drawing

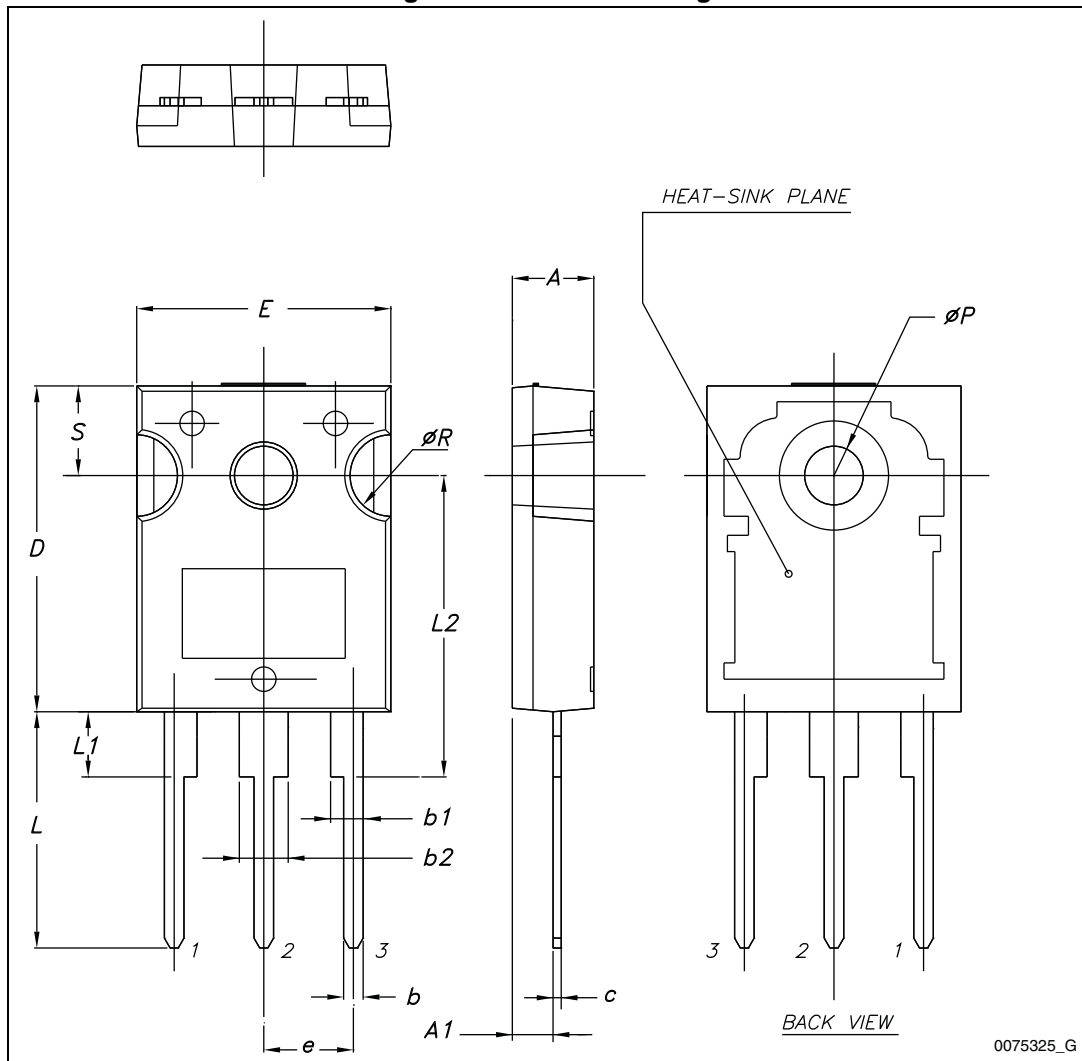


Table 8. TO-247 mechanical data

| Dim. | mm. | | |
|------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 4.85 | | 5.15 |
| A1 | 2.20 | | 2.60 |
| b | 1.0 | | 1.40 |
| b1 | 2.0 | | 2.40 |
| b2 | 3.0 | | 3.40 |
| c | 0.40 | | 0.80 |
| D | 19.85 | | 20.15 |
| E | 15.45 | | 15.75 |
| e | 5.30 | 5.45 | 5.60 |
| L | 14.20 | | 14.80 |
| L1 | 3.70 | | 4.30 |
| L2 | | 18.50 | |
| ØP | 3.55 | | 3.65 |
| ØR | 4.50 | | 5.50 |
| S | 5.30 | 5.50 | 5.70 |

Figure 28. TO-3P drawing



Table 9. TO-3P mechanical data

| Dim. | mm | | |
|------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 4.60 | | 5 |
| A1 | 1.45 | 1.50 | 1.65 |
| A2 | 1.20 | 1.40 | 1.60 |
| b | 0.80 | 1 | 1.20 |
| b1 | 1.80 | | 2.20 |
| b2 | 2.80 | | 3.20 |
| c | 0.55 | 0.60 | 0.75 |
| D | 19.70 | 19.90 | 20.10 |
| D1 | | 13.90 | |
| E | 15.40 | | 15.80 |
| E1 | | 13.60 | |
| E2 | | 9.60 | |
| e | 5.15 | 5.45 | 5.75 |
| L | 19.50 | 20 | 20.50 |
| L1 | | 3.50 | |
| L2 | 18.20 | 18.40 | 18.60 |
| øP | 3.10 | | 3.30 |
| Q | | 5 | |
| Q1 | | 3.80 | |

5 Revision history

Table 10. Document revision history

| Date | Revision | Changes |
|-------------|----------|--|
| 13-Jan-2014 | 1 | Initial release. |
| 03-Feb-2014 | 2 | Added $V_{CE(sat)}$ max value in Table 5: Dynamic characteristics . Minor text changes. |

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